NPN Epitaxial Planar Silicon Composite Transistors



CPH6519

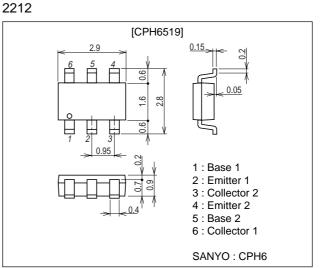
Low-Frequency General-Purpose **Amplifier, Driver Applications**

Features

- Composite type with 2 transistors contained in the CPH package currently in use, improving the mounting efficiency greatly.
- The CPH6519 is formed with two chips, being equivalent to the 2SC3689, placed in one package.
- · Adoption of FBET process.
- High DC current gain (hFE=800 to 3200).
- High VEBO (VEBO≥15V).
- Excellent in thermal equilibrium and pair capability.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		60	V
Collector-to-Emitter Voltage	VCEO		50	V
Emitter-to-Base Voltage	VEBO		15	V
Collector Current	IC		100	mA
Collector Current (Pulse)	ICP		200	mA
Base Current	IB		20	mA
Collector Dissipation	PC	1unit	350	mW
Total Dissipation	Рт		500	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =40V, I _E =0			0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =10V, I _C =0			0.1	μA
DC Current Gain	hFE	V _{CE} =5V, I _C =10mA	800	1500	3200	
DC Current Gain Ratio	hFE(small/ large)	VCE=5V, IC=10mA	0.8	0.98		
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Marking: 3F

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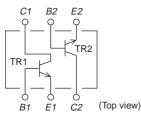
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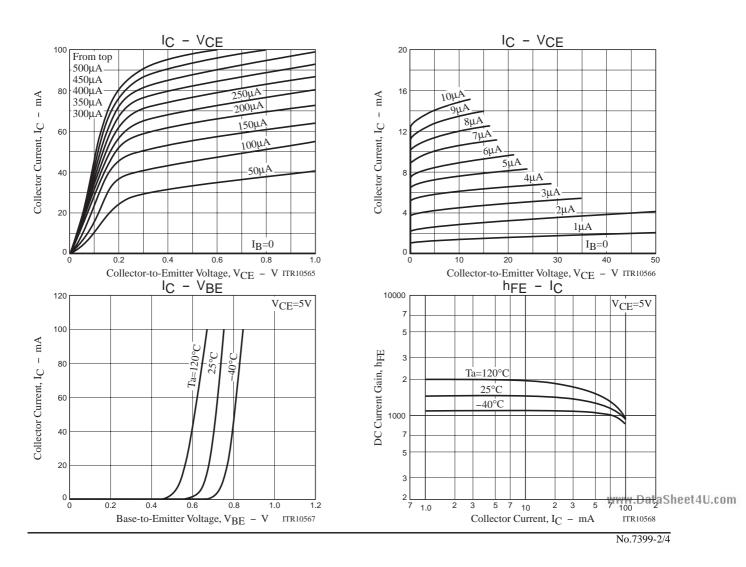
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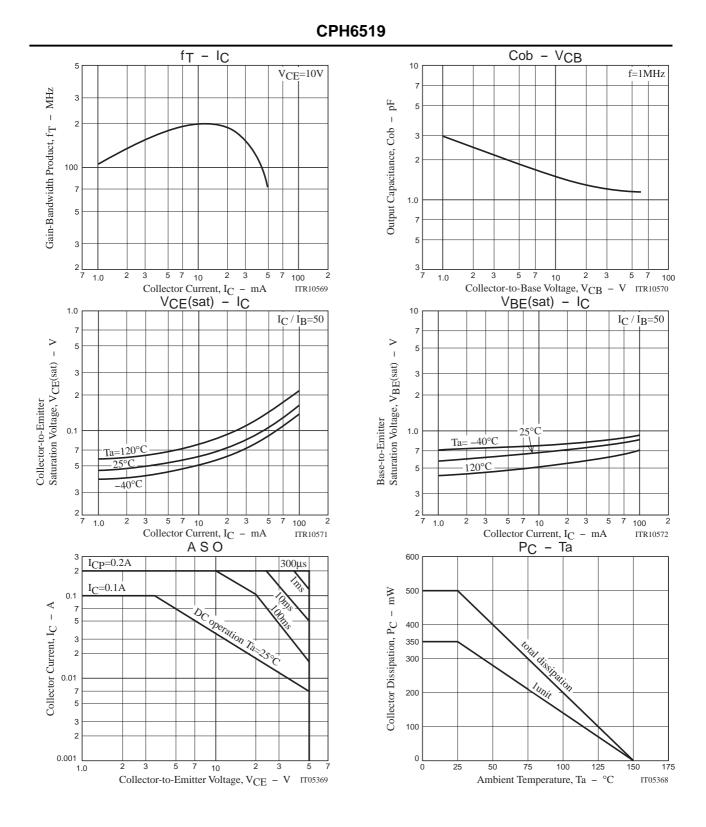
Parameter	Symbol	Conditions	Ratings			1.1-14
			min	typ	max	Unit
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =10mA		200		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		1.5		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=50mA, IB=1mA		0.1	0.5	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=50mA, IB=1mA		0.8	1.1	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0	60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0	15			V

Note : The specifications shown above are for each individual transistor.

Electrical Connection







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